

GOD-230T

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|--|---|
| 1. Color | Red |
| 2. Material | AlGaInP / GaP |
| 3. Electrode | N(cathode) side : Au / P(anode) side : Au |
| 4. Electrode pattern | (Fig.) |
| 5. Chip size | 0.22 mm × 0.22 mm × 0.20 mmH (Fig.) |
| 6. Chip structure | Face up: wire bonding |
| 7. Electro-Optical characteristics (Ta = 25°C) | |

Parameters	Symbol	Condition	Characteristics			Unit
			Min.	Typ.	Max.	
Brightness*	Iv	IF = 20mA	400	450	—	mcd
Forward Voltage	VF	IF = 20mA	1.9	2.2	2.4	V
Reverse Current	IR	VR = 5V	—	—	10	μA
Dominant Wavelength	λd	IF = 20mA	620	625	630	nm

*Brightness Measurement at Resonac Photonics.

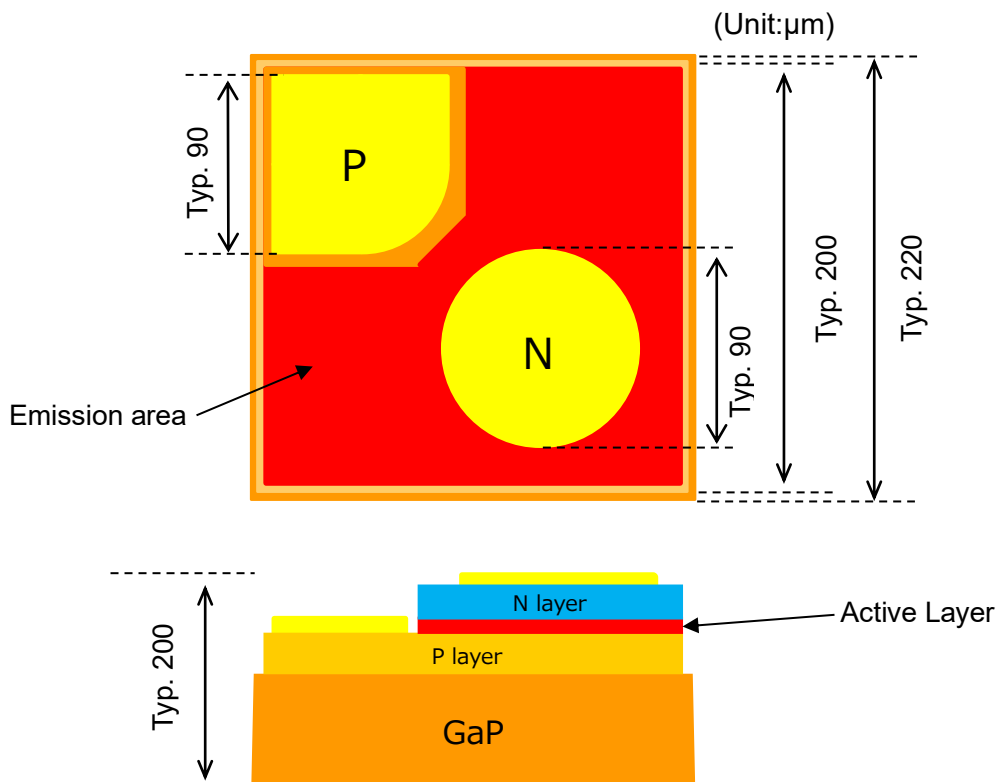


Fig. Chip size & Emission area

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